

Description

This 60V,100A N-Channel MOSFET in a TO-263 Plastic Package.

Features

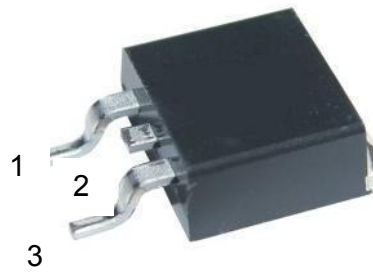
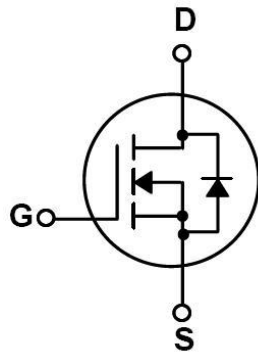
- Low gate charge
- Low crss
- Fast Switching
- Halogen-free Product

Applications

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies

V_{DSS}	$R_{DS(on)}$ (Typ)	I_D
60V	5.9mΩ	100A

Equivalent Circuit & Pinning



Pin1:Gate

Pin2:Drain

Pin3:Source

Absolute Maximum Ratings(Ta=25°C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	60	V
Drain Current	$I_D(T_C=25^\circ\text{C})$	100	A
Peak Drain Current	I_{DM}	380	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulsed Avalanche Energy	E_{AS}	602	mJ
Avalanche Current	I_{AS}	38.9	A
Total Power Dissipation	$P_D(T_C=25^\circ\text{C})$	188	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C
Thermal Resistance-Junction to Case	$R_{\theta JC}$	0.8	°C/W
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	62.5	

Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V$ $V_{GS}=0V$			1	μA
		$V_{DS}=60V$ $V_{GS}=0V$ $T_J=125^\circ\text{C}$			10	μA
Gate-Body leakage current	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2	2.6	4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V$ $I_D=50A$		5.9	7	m Ω

Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Diode Forward Voltage	V _{SD}	I _S =1A V _{GS} =0V		0.6	1.2	V
Input Capacitance	C _{iss}	V _{GS} =0V V _{DS} =25V, f=1.0MHz		4920		pF
Output Capacitance	C _{oss}			295		
Reverse Transfer Capacitance	C _{rss}			133		
Gate resistance	R _g	V _{GS} =0V V _{DS} =0V, f=1MHz		1.2		Ω
Total Gate Charge	Q _g (10V)	V _{GS} =10V V _{DS} =30V I _D =50A		53	75	nC
Total Gate Charge	Q _g (4.5V)			22	31	
Gate Source Charge	Q _{gs}			17		
Gate Drain Charge	Q _{gd}			5		
Turn-On DelayTime	t _{D(on)}	V _{DD} =30V I _D =50A V _{GS} =10V R _G =2.5Ω		18		ns
Turn-On Rise Time	t _r			20		
Turn-Off DelayTime	t _{D(off)}			33		
Turn-Off Fall Time	t _f			4		

- A. The value of R_{qJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation PDSM is based on R_{qJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150°C may be used if the PCB allows it.
- B. The power dissipation PD is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.
- D. The R_{qJA} is the sum of the thermal impedance from junction to case R_{qJC} and case to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300ms pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating.
- G. The maximum current limited by package.
- H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

Electrical Characteristic Curve

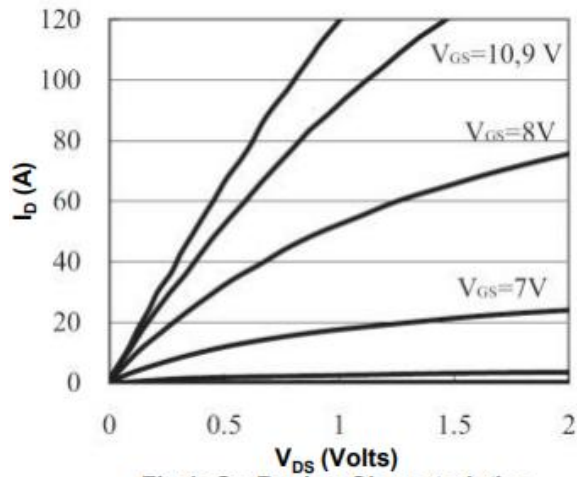


Fig 1: On-Region Characteristics

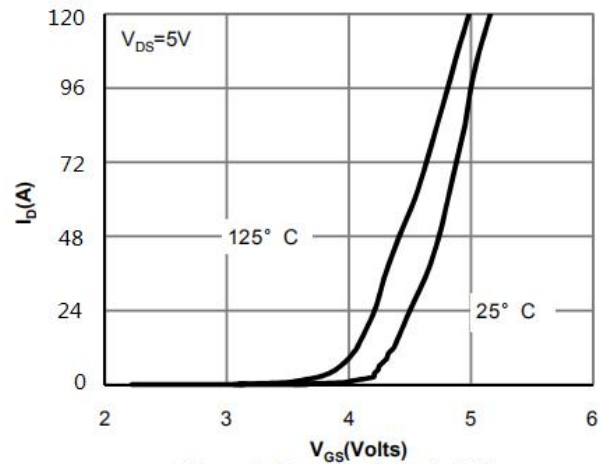


Figure 2: Transfer Characteristics

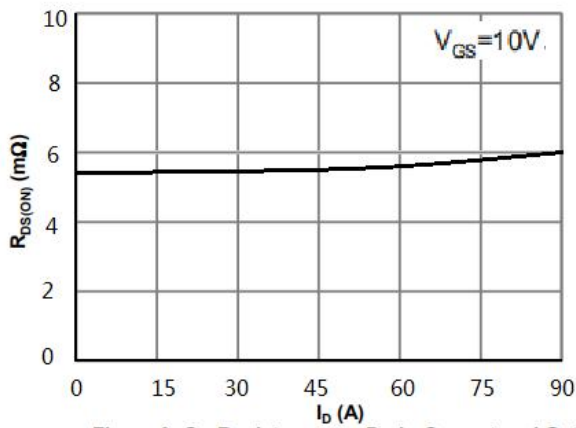


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

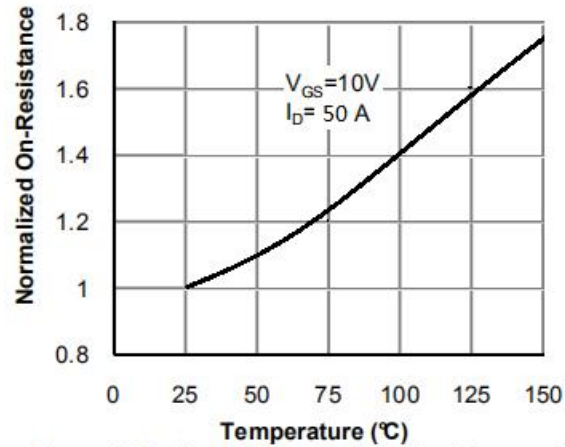


Figure 4: On-Resistance vs. Junction Temperature

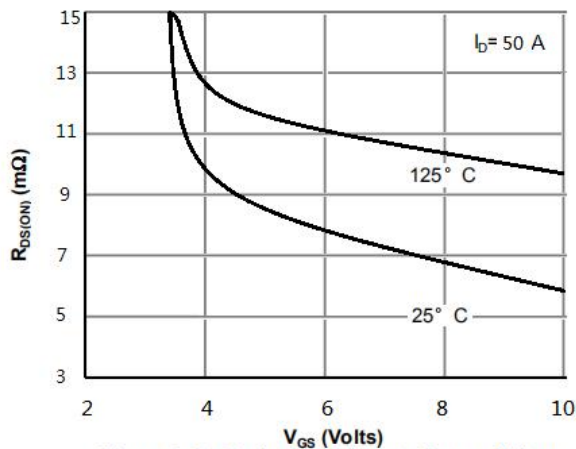


Figure 5: On-Resistance vs. Gate-Source Voltage

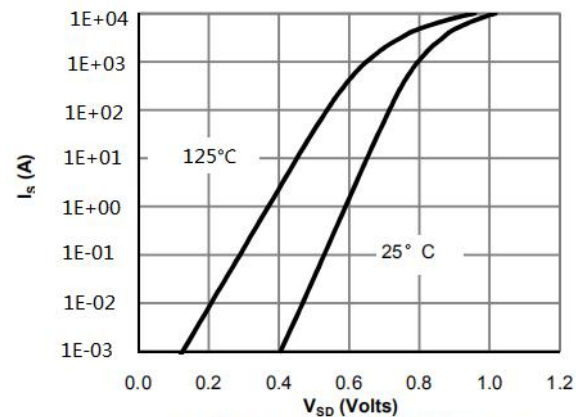


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve

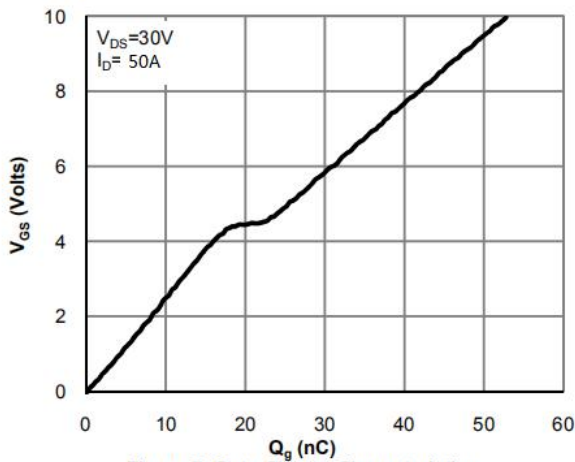


Figure 7: Gate-Charge Characteristics

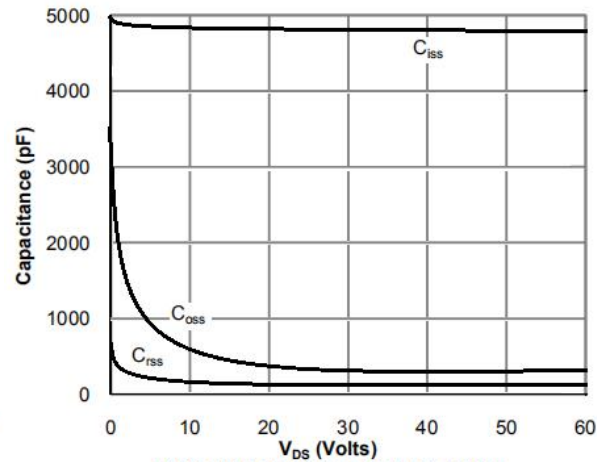


Figure 8: Capacitance Characteristics

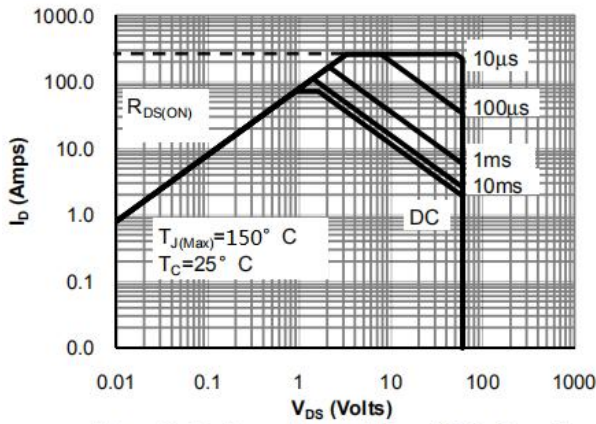


Figure 9: Maximum Forward Biased Safe Operating Area

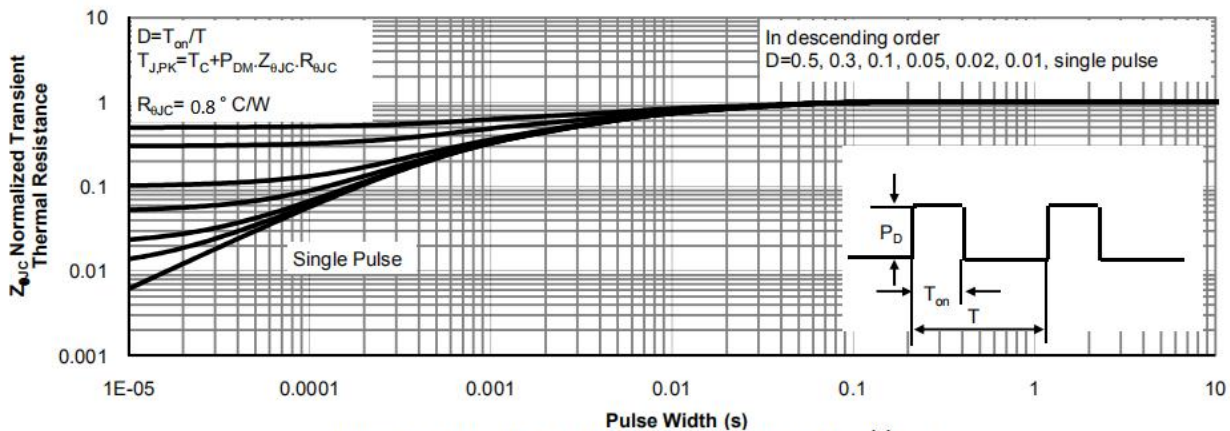
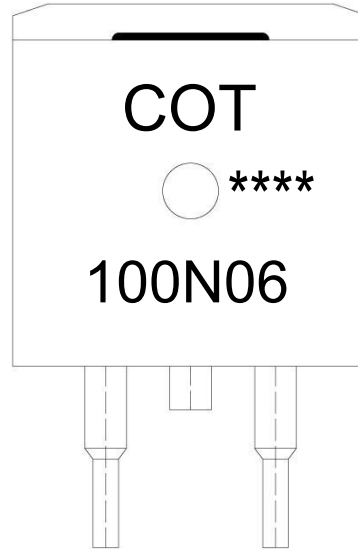


Figure 10 : Normalized Maximum Transient Thermal Impedance

Marking Instructions



Note:

COT: Company Logo

100N06: Product Type.

****: Lot No. Code, code change with Lot No.

Packaging SPEC.

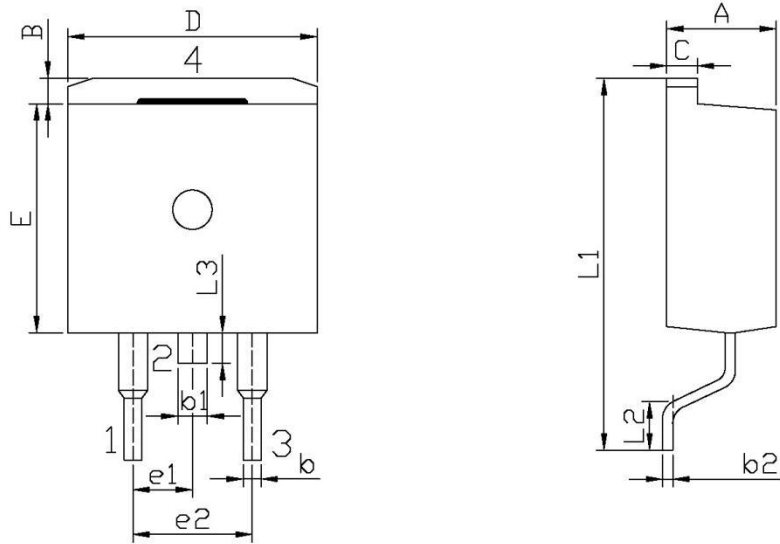
REEL INFORMATION

Package Type	Units					Dimension (unit: mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-263	800	1	800	5	4,000	13" x24	360×360×50	385×257×392

TUBE INFORMATION

Package Type	Units					Dimension (unit: mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-263	50	20	1,000	5	5,000	532×33×7.0	555×164×50	575×290×180

Package Outline Dimensions



单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.30	4.70	E	9.00	9.40
B	1.00	1.40	e1	2.34	2.74
b	0.70	0.90	e2	4.88	5.28
b1	1.15	1.35	L1	15.00	16.00
b2	0.40	0.60	L2	2.24	2.84
C	1.20	1.40	L3	1.20	1.60
D	9.80	10.20			

T0-263